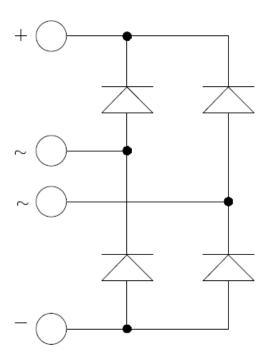
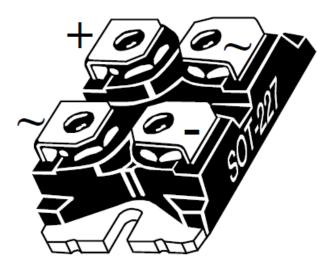


## **MSC50DC70HJ SiC Diode Full Bridge Power Module**

## 1 Product Overview

This section shows the product overview of the MSC50DC70HJ device.





All ratings at  $T_j = 25$ °C, unless otherwise specified.

**Caution**: These devices are sensitive to electrostatic discharge. Proper handling procedures should be followed.



#### 1.1 Features

The following are key features of the MSC50DC70HJ device:

- Silicon carbide (SiC) Schottky diode
  - Zero reverse recovery
  - Zero forward recovery
  - Temperature-independent switching behavior
  - Positive temperature coefficient on VF
- Very low stray inductance
- High level of integration

#### 1.2 Benefits

The following are benefits of the MSC50DC70HJ device:

- Outstanding performance at high-frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction-to-case thermal resistance
- RoHS compliant

## 1.3 Applications

The MSC50DC70HJ device is designed for the following applications:

- Switch-mode power supplies rectifier
- Induction heating
- Welding equipment
- High-speed rectifiers



## **2** Electrical Specifications

This section shows the electrical specifications of the MSC50DC70HJ device.

### 2.1 Absolute Maximum Ratings

The following table shows the absolute maximum ratings per SiC diode of the MSC50DC70HJ device.

**Table 1 • Absolute Maximum Ratings** 

Symbol	Parameter	Maximum Ratings	Unit	
V <sub>RRM</sub>	Repetitive peak reverse voltage		700	V
l <sub>F</sub>	DC forward current	Tc = 25 °C	50	Α

The following table shows the thermal and package characteristics of the MSC50DC70HJ.

**Table 2 • Thermal and Package Characteristics** 

Symbol	Characteristic	Min	Тур	Max	Unit
Visol	RMS isolation voltage, any terminal to case t =1 minute, 50 Hz/60 Hz	2500			V
Tı, Tstg	Storage temperature range	<b>-</b> 55		175	°C
Тлор	Recommended junction temperature under switching conditions	<b>-</b> 55		T <sub>Jmax</sub> – 25	<del></del>
Torque	Terminals and mounting screws			1.1	N.m
Wt	Package weight		29.2		g

### 2.2 Electrical Performance

The following table shows the electrical characteristics per SiC diode of the MSC50DC70HJ.

**Table 3 • Electrical Characteristics** 

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
VF	Diode forward voltage	I <sub>F</sub> = 50 A	T <sub>j</sub> = 25 °C		1.5	1.8	V
			T <sub>j</sub> = 175 °C		1.9		≘
Irм	Reverse leakage current	$V_R = 700 \ V$	T <sub>j</sub> = 25 °C		15	200	μΑ
			T <sub>j</sub> = 175 °C		250		≡
<b>Q</b> c	Total capacitive charge	V <sub>R</sub> = 400 V			133		nC
С	Total capacitance	f = 1 MHz, V <sub>R</sub> = 200 V			248		pF
		f = 1 MHz, V <sub>R</sub> = 400	) V		216		≘
RthJC	Junction-to-case thermal resistance					1.46	°C/W



## 2.3 Performance Curves

This section shows the typical performance curves of the MSC50DC70HJ device.

Figure 1 • Maximum Transient Thermal Impedance

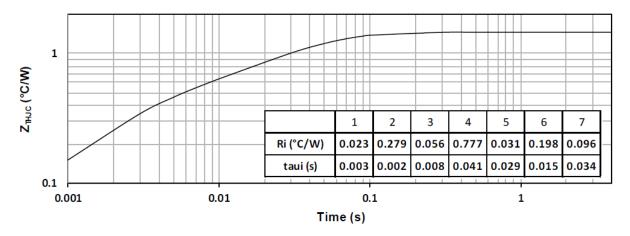


Figure 2 • Forward Current vs. Forward Voltage

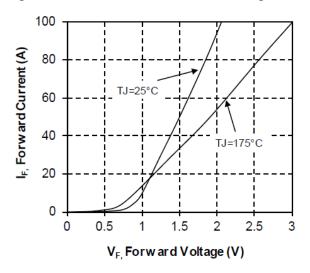
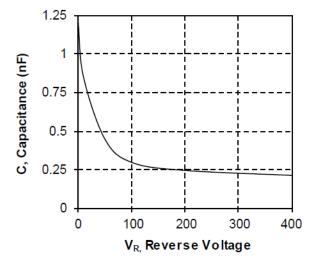


Figure 3 • Capacitance vs. Reverse Voltage





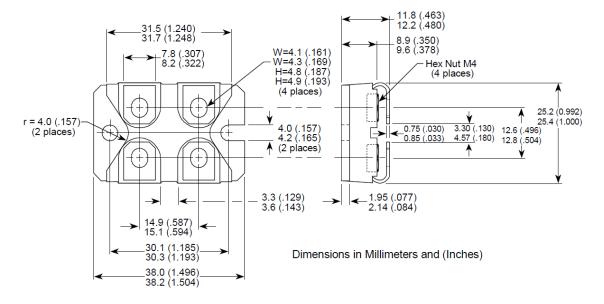
## **3** Package Specification

This section shows the package specification of the MSC50DC70HJ device.

## 3.1 Package Outline Drawing

The package outline of the MSC50DC70HJ device is illustrated in this section.

Figure 4 ● Package Outline Drawing







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